

~~27~~ (new) A CVD apparatus as stated in claim 25, wherein the switch includes a first station for connecting the partitioning wall to the RF power supply for feeding a cleaning RF power and a second station for connecting the partitioning wall to a ground for cleaning using the RF power supplied to the radio-frequency electrode in the first chamber.

~~27~~ (new) A CVD apparatus as stated in claim 17, further comprising an RF power supply for feeding a cleaning RF power and a switch for connecting the partitioning wall section to the RF power supply with suitable timing so as to produce a cleaning plasma in the film deposition process space.

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~~28~~ (new) A CVD apparatus as stated in claim 20, wherein the connecting means includes a switch which selectively connects the partitioning wall to the RF power supply for feeding a cleaning RF power and to a ground for cleaning using the RF power supplied to the radio-frequency electrode in the first chamber.

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~~29~~ (new) A CVD apparatus as stated in claim 28, wherein the switch includes a first station for connecting the partitioning wall to the RF power supply for feeding a cleaning RF power and a second station for connecting the partitioning wall to a ground for cleaning using the RF power supplied to the radio-frequency electrode in the first chamber.

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31. (new) A CVD apparatus as stated in claim 1, further comprising a circuit for connecting the partitioning wall to ground while a cleaning power is applied to the radio-frequency electrode so as to produce a cleaning plasma in the film deposition process space.

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